
2SJ218

Silicon P-Channel MOS FET

HITACHI

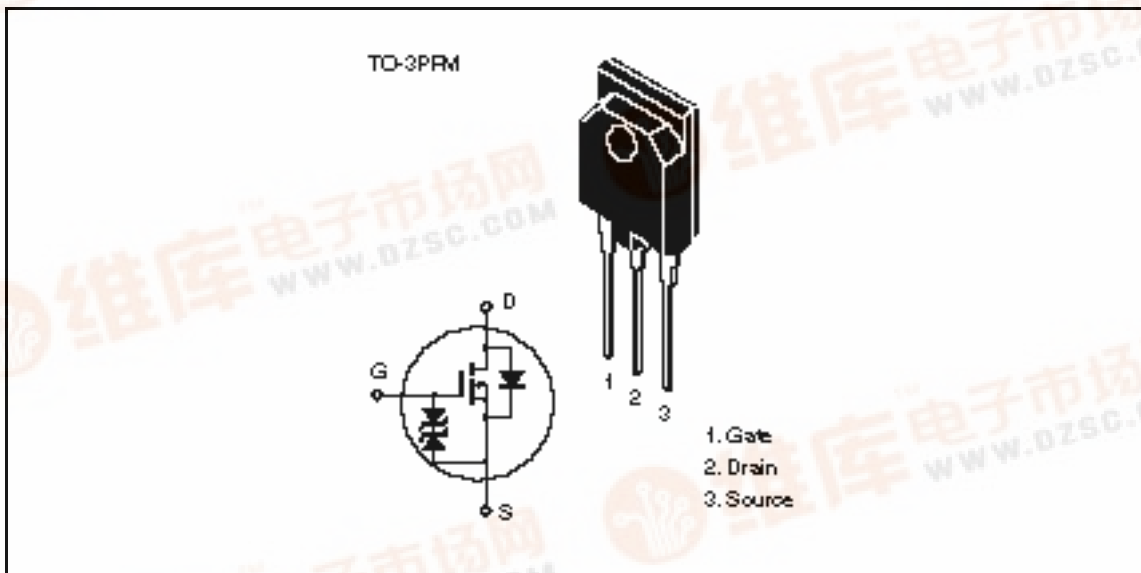
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- 4 V gate drive device
 - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-60	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	-45	A
Drain peak current	$I_{D(pulse)}^{*1}$	-180	A
Body to drain diode reverse drain current	I_{DR}	-45	A
Channel dissipation	P_{ch}^{*2}	60	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW 10 μs, duty cycle 1%

2. Value at T_c = 25°C

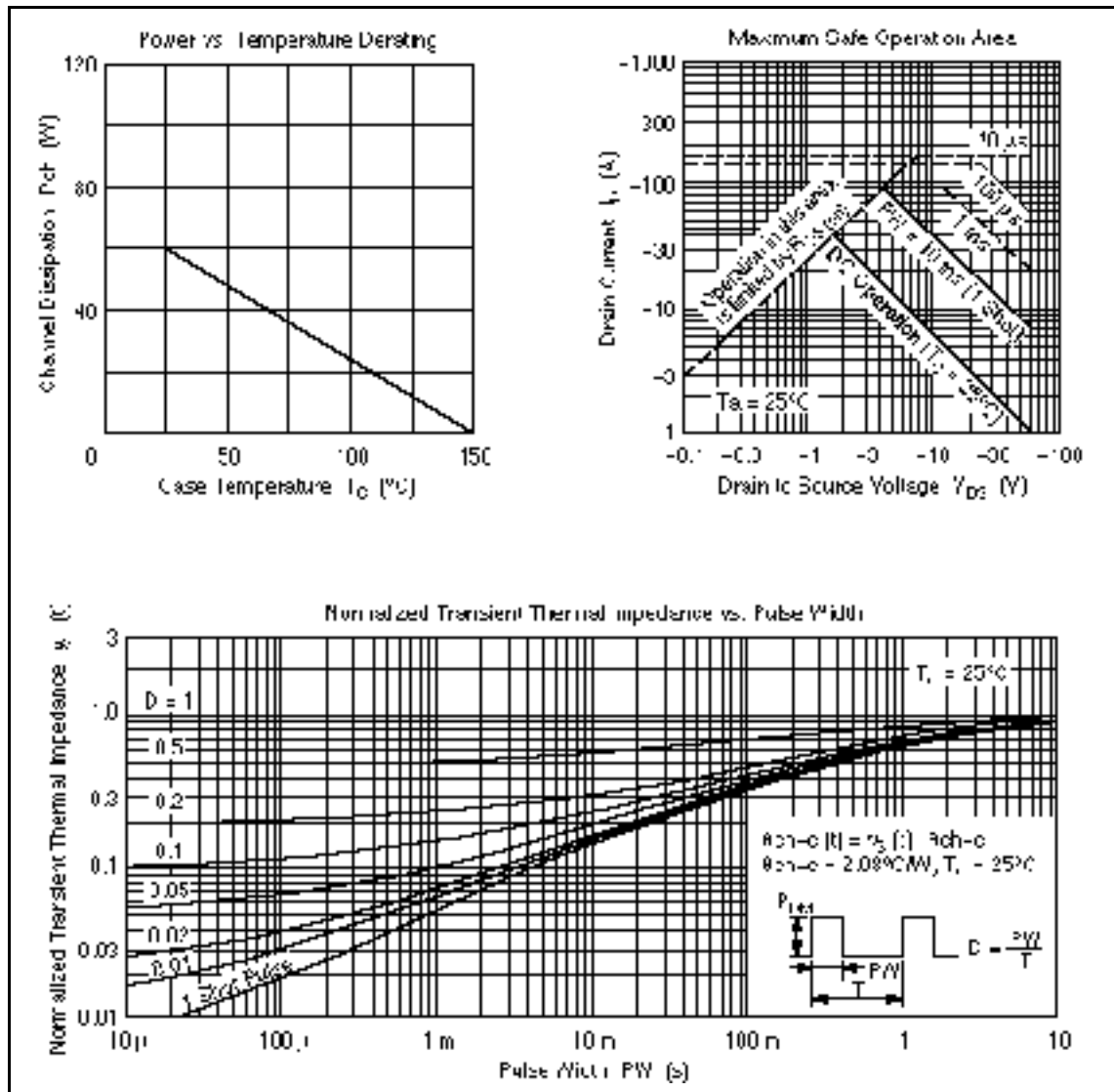
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-250	μA	$V_{DS} = -50 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.033	0.042		$I_D = -20 \text{ A}, V_{GS} = -10 \text{ V}^{*1}$
			—	0.045		0.06
Forward transfer admittance	$ y_{fs} $	16	25	—	S	$I_D = -20 \text{ A}, V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	3800	—	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0,$
Output capacitance	C_{oss}	—	2000	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	C_{rss}	—	490	—	pF	
Turn-on delay time	$t_{d(on)}$	—	30	—	ns	$I_D = -20 \text{ A}, V_{GS} = -10 \text{ V},$
Rise time	t_r	—	235	—	ns	$R_L = 1.5$
Turn-off delay time	$t_{d(off)}$	—	670	—	ns	
Fall time	t_f	—	450	—	ns	
Body to drain diode forward voltage	V_{DF}	—	-1.35	—	V	$I_F = -45 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	300	—	ns	$I_F = -45 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

See characteristic curves of 2SJ217

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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-4835
U.S.A.
Tel: 415-589-8300
Fax: 415-589-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 94 80 0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitbrook Park
Lower Cookham Road
M Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-885000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
45 Collyer Quay #20-00
Hitachi Tower
Singapore 0404
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 705, North Tower,
World Finance Centre
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27308074